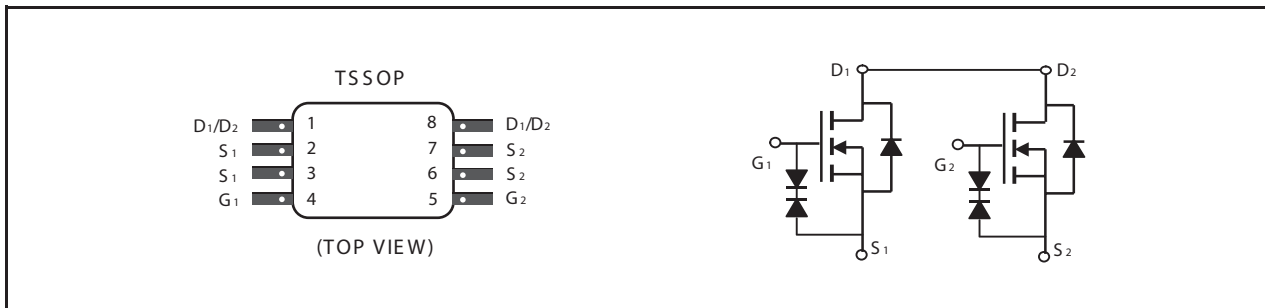


**Dual N-Channel Enhancement Mode Field Effect Transistor****PRODUCT SUMMARY**

| VDSS | ID | RDS(ON) (mΩ) Max |
|------|----|------------------|
| 20V | 7A | 20 @ VGS=4.0V |
| | | 27 @ VGS=2.5V |

FEATURES

- Super high dense cell design for low RDS(ON).
- Rugged and reliable.
- Surface Mount Package.
- ESD Protected.

**ABSOLUTE MAXIMUM RATINGS (TA=25°C unless otherwise noted)**

| Symbol | Parameter | Limit | Units |
|-----------------------------------|--|----------------------|-------|
| V _{DS} | Drain-Source Voltage | 20 | V |
| V _{GS} | Gate-Source Voltage | ±12 | V |
| I _D | Drain Current-Continuous ^a | T _A =25°C | 7 |
| | | T _A =70°C | 5.6 |
| I _{DM} | -Pulsed ^b | 28 | A |
| P _D | Maximum Power Dissipation ^a | T _A =25°C | 1.5 |
| | | T _A =70°C | 1 |
| T _J , T _{STG} | Operating Junction and Storage Temperature Range | -55 to 150 | °C |

THERMAL CHARACTERISTICS

| Symbol | Parameter | Limit | Units |
|------------------|--|-------|-------|
| R _{θJA} | Thermal Resistance, Junction-to-Ambient ^a | 85 | °C/W |

STG8820

Ver 1.1

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

| Symbol | Parameter | Conditions | Min | Typ | Max | Units |
|---|---|---|-----|------|-----|-------|
| OFF CHARACTERISTICS | | | | | | |
| BV _{DSS} | Drain-Source Breakdown Voltage | V _{GS} =0V, I _D =250μA | 20 | | | V |
| I _{DSS} | Zero Gate Voltage Drain Current | V _{DS} =16V, V _{GS} =0V | | | 1 | μA |
| I _{GSS} | Gate-Body Leakage Current | V _{GS} = ±12V, V _{DS} =0V | | | ±10 | μA |
| ON CHARACTERISTICS | | | | | | |
| V _{GS(th)} | Gate Threshold Voltage | V _{DS} =V _{GS} , I _D =250μA | 0.5 | 0.8 | 1.5 | V |
| R _{DS(ON)} | Drain-Source On-State Resistance | V _{GS} =4V, I _D =7A | | 17 | 20 | m ohm |
| | | V _{GS} =2.5V, I _D =6A | | 20 | 27 | m ohm |
| g _{FS} | Forward Transconductance | V _{DS} =5V, I _D =7A | | 23 | | S |
| DYNAMIC CHARACTERISTICS ^c | | | | | | |
| C _{ISS} | Input Capacitance | V _{DS} =10V, V _{GS} =0V f=1.0MHz | | 470 | | pF |
| C _{OSS} | Output Capacitance | | | 164 | | pF |
| C _{RSS} | Reverse Transfer Capacitance | | | 142 | | pF |
| SWITCHING CHARACTERISTICS ^c | | | | | | |
| t _{D(ON)} | Turn-On Delay Time | V _{DD} =10V I _D =1A V _{GS} =4V R _{GEN} =10 ohm | | 17 | | ns |
| t _r | Rise Time | | | 54 | | ns |
| t _{D(OFF)} | Turn-Off Delay Time | | | 63 | | ns |
| t _f | Fall Time | | | 45 | | ns |
| Q _g | Total Gate Charge | V _{DS} =10V, I _D =7A, V _{GS} =4V | | 10 | | nC |
| Q _{gs} | Gate-Source Charge | | | 2.1 | | nC |
| Q _{gd} | Gate-Drain Charge | | | 4.5 | | nC |
| DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS | | | | | | |
| I _S | Maximum Continuous Drain-Source Diode Forward Current | | | | 2.0 | A |
| V _{SD} | Diode Forward Voltage ^b | V _{GS} =0V, I _S =2.0A | | 0.79 | 1.2 | V |

Notes

- a. Surface Mounted on FR4 Board, t ≤ 10sec.
 b. Pulse Test: Pulse Width ≤ 300us, Duty Cycle ≤ 2%.
 c. Guaranteed by design, not subject to production testing.

Mar, 29, 2010

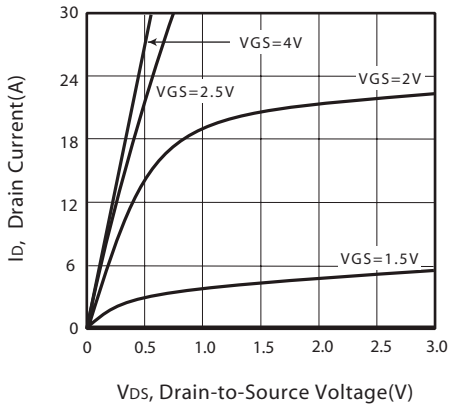


Figure 1. Output Characteristics

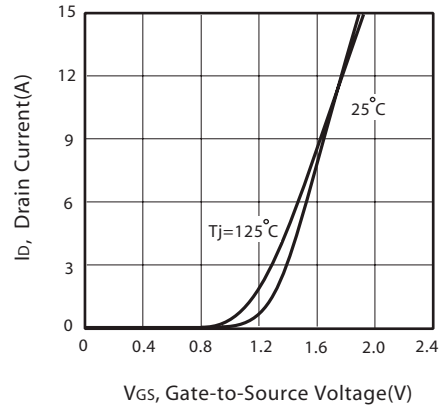


Figure 2. Transfer Characteristics

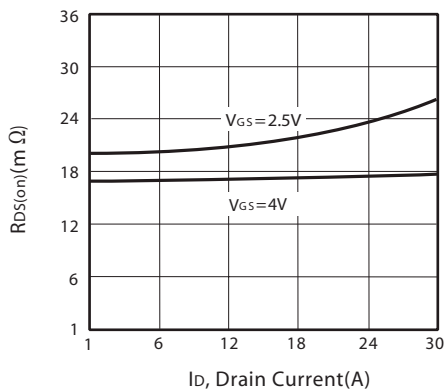


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

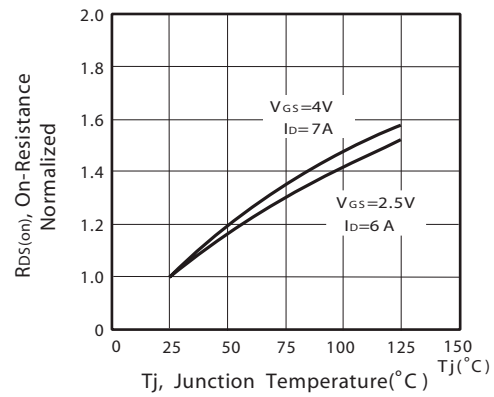


Figure 4. On-Resistance Variation with Drain Current and Temperature

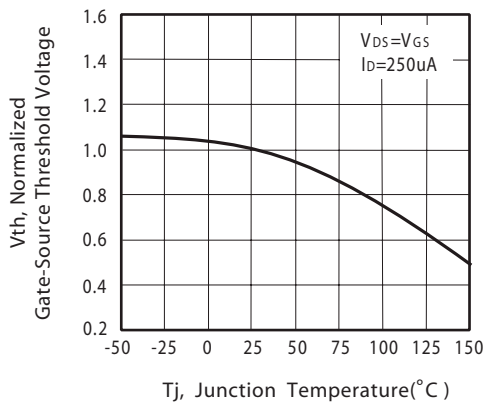


Figure 5. Gate Threshold Variation with Temperature

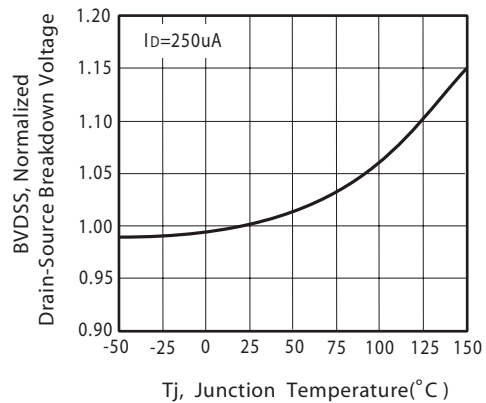


Figure 6. Breakdown Voltage Variation with Temperature

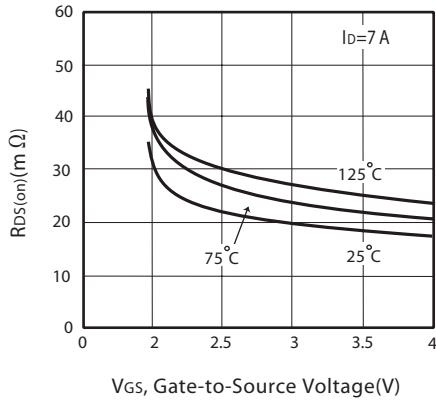


Figure 7. On-Resistance vs. Gate-Source Voltage

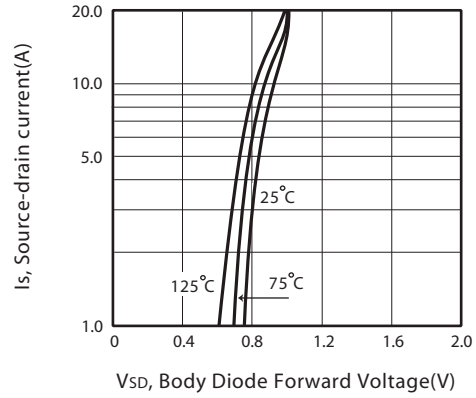


Figure 8. Body Diode Forward Voltage Variation with Source Current

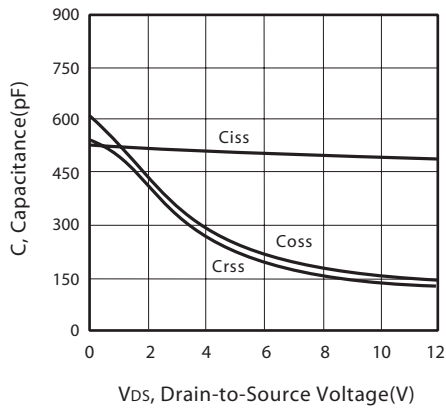


Figure 9. Capacitance

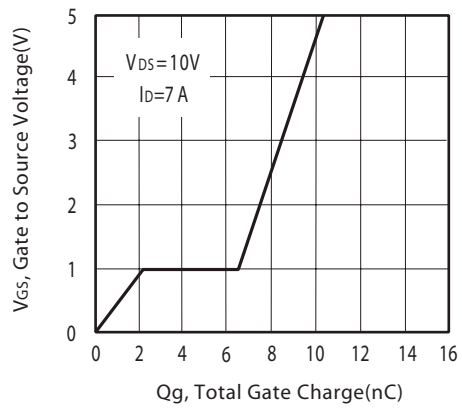


Figure 10. Gate Charge

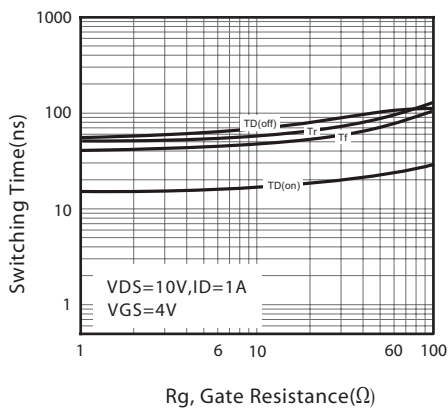


Figure 11. switching characteristics

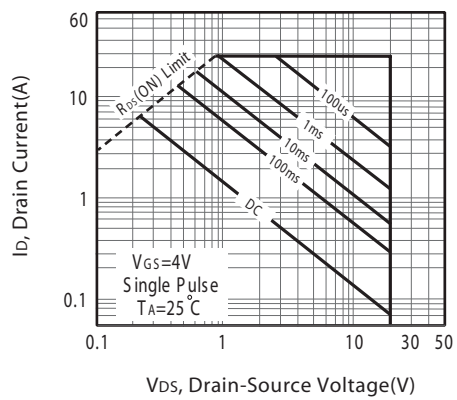


Figure 12. Maximum Safe Operating Area

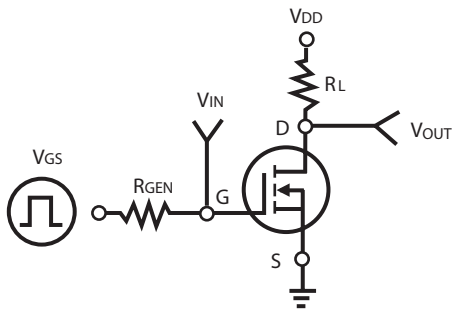


Figure 13. Switching Test Circuit

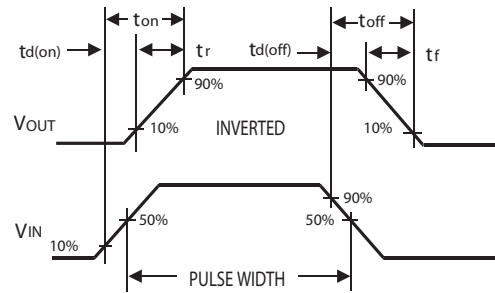
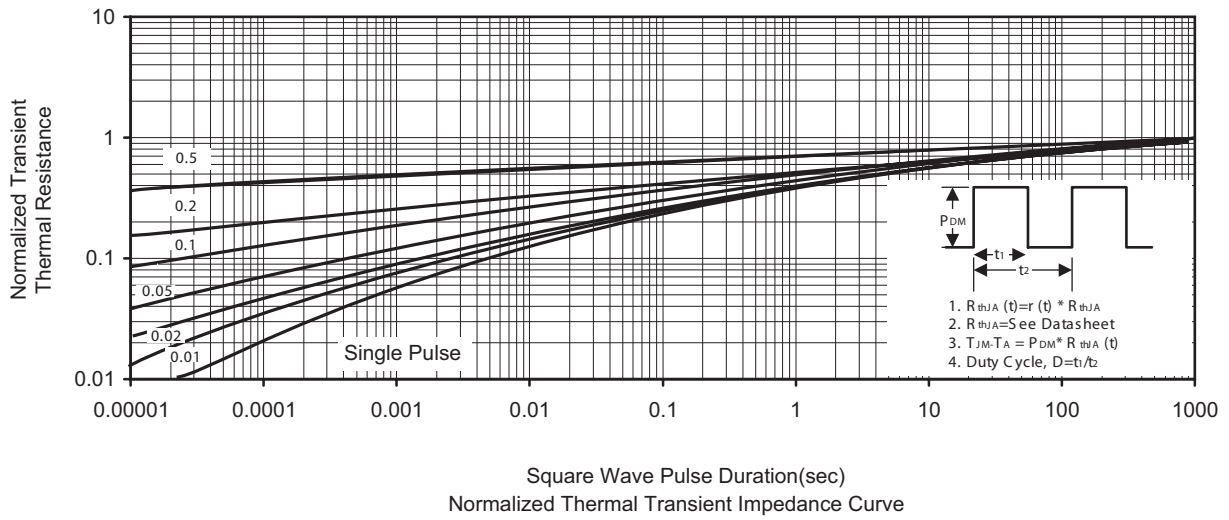
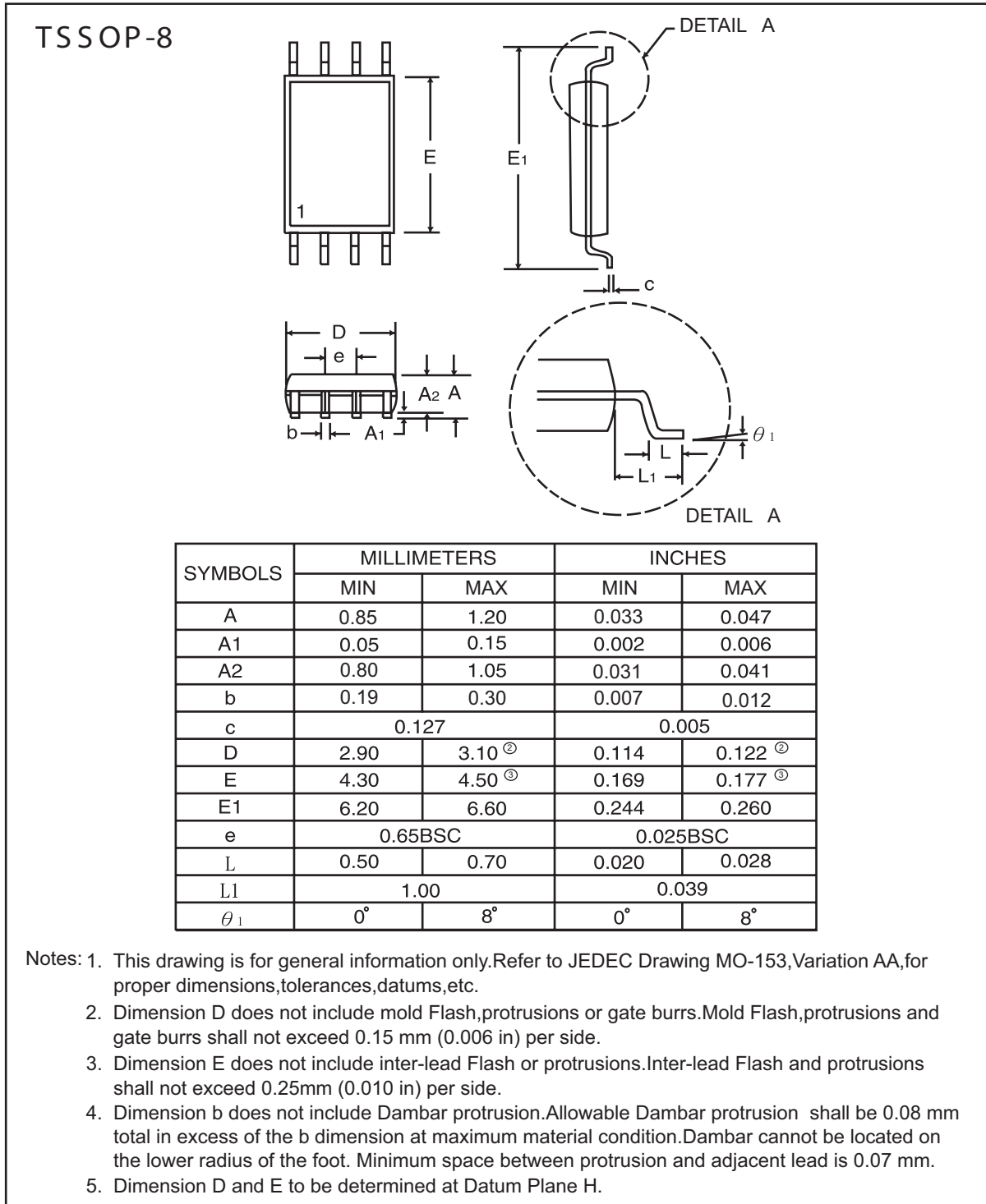


Figure 14. Switching Waveforms

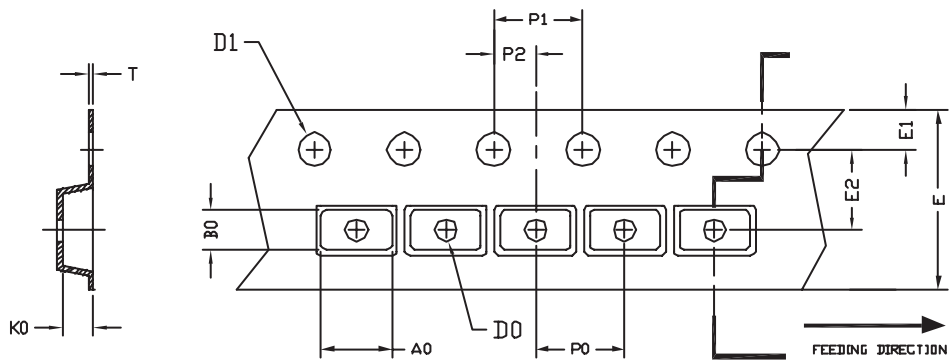


PACKAGE OUTLINE DIMENSIONS



TSSOP-8 Tape and Reel Data

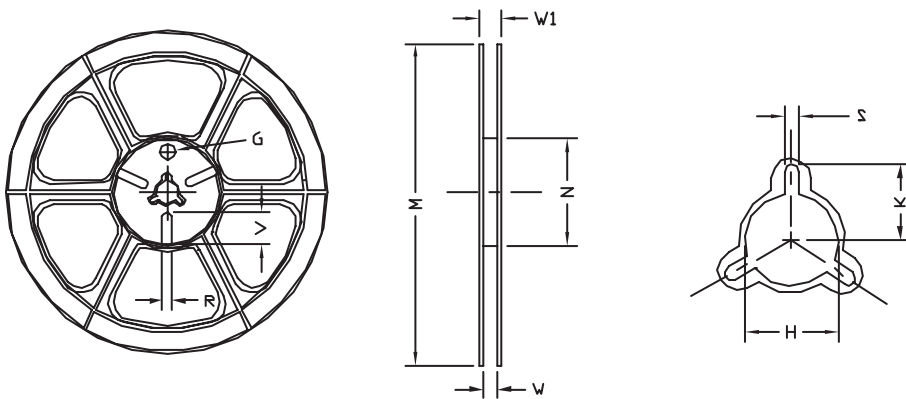
TSSOP-8 Carrier Tape



UNIT : mm

| PACKAGE | A0 | B0 | K0 | D0 | D1 | E | E1 | E2 | P0 | P1 | P2 | T |
|------------|------|------|------|-----------------------------|-----------------------------|--------------------|------|--------------------|------|------|--------------------|--------------------|
| TSSOP 8 | 6.08 | 4.40 | 1.60 | $\phi 1.50$ +0.1 -0.0 | $\phi 1.50$ +0.1 -0.0 | 12.00 ± 0.3 | 1.75 | 5.50 ± 0.05 | 8.00 | 4.00 | 2.00 ± 0.05 | 0.30 ± 0.05 |

TSSOP-8 Reel



UNIT : mm

| TAPE SIZE | REEL SIZE | M | N | W | W1 | H | K | S | G | R | V |
|-----------|------------|-----|-----|------|------|-----------------------------|------|------------------|-----|-----|-----|
| 12 mm | $\phi 330$ | 330 | 100 | 12.5 | 16.0 | $\phi 13.0$ +0.5 -0.2 | 10.6 | 2.0 ± 0.5 | --- | --- | --- |